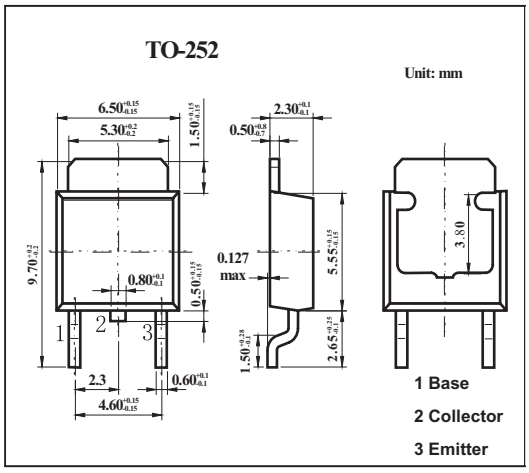
Silicon NPN Triple Diffused

2SC4499S



Features

- High speed and high voltage switching

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	500	V
Collector to emitter voltage	V_{CEO}	400	V
Emitter to base voltage	V_{EBO}	10	V
Collector current	I_{CP}	0.5	A
Collector peak current	I_C	1	A
Collector power dissipation	P_C	0.75	W
TC=25℃		10	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to emitter sustain voltage	$V_{CEO(sus)}$	I_C = 0.1 A, R_{BE} = ∞,L = 100 mH	400			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	I_E = 10 mA, I_C = 0	10			V
Collector cutoff current	I_{CBO}	V_{CB} = 400 V, I_E = 0			20	μA
	I_{CEO}	V_{CE} = 350 V, R_{BE} = ∞			50	
DC current transfer ratio	h_{FE}	V_{CE} = 5 V, I_C = 0.25 A*1	12			
		V_{CE} = 5 V, I_C = 0.5 A*1	5			
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = 0.25 A, I_B = 0.05 A*1			1.0	V
Base to emitter saturation voltage	$V_{BE(sat)}$	I_C = 0.25 A, I_B = 0.05 A*1			1.5	V
Turn on time	t_{on}	I_C = 0.5 A, I_{B1} = -I_{B2} = 0.1 A,			1.0	μs
Storage time	t_{stg}	V_{CC}= 150 V			2	μs
Fall time	t_f				1.0	μs

* 1 Pulse test.